

## isc N-Channel MOSFET Transistor

**IXTH12N65X2**

### • FEATURES

- Drain Source Voltage-  
:  $V_{DSS} = 650V$ (Min)
- Static drain-source on-resistance:  
 $R_{DS(on)} \leq 300m\Omega @ V_{GS}=10V$
- Fully characterized avalanche voltage and current
- 100% Avalanche Tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### • APPLICATION

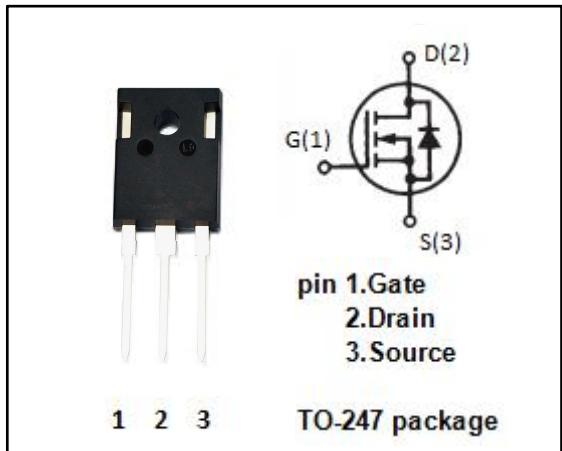
- Switched mode power supplies
- DC-DC converters

### • ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

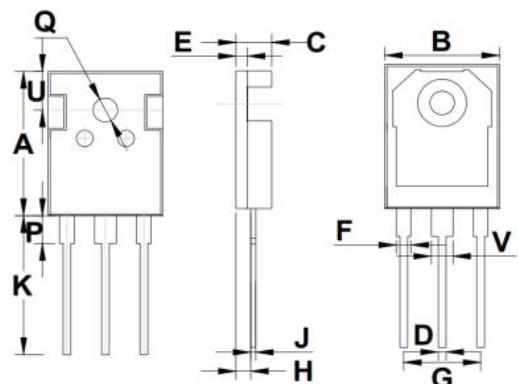
SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage	650	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current-Continuous	12	A
$I_{DM}$	Drain Current-Single Pulsed	24	A
$P_D$	Total Dissipation @ $T_c=25^\circ C$	180	W
$T_j$	Operating Junction Temperature	-55~150	°C
$T_{stg}$	Storage Temperature	-55~150	°C

### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(j-c)}$	Junction-to-case thermal resistance	0.69	°C/W



TO-247 package



DIM	MM	
	MIN	MAX
A	19.80	20.20
B	15.40	15.80
C	4.90	5.10
D	0.90	1.10
E	1.40	1.60
F	1.90	2.10
G	10.80	11.00
H	2.40	2.60
J	0.50	0.70
K	19.50	20.50
P	3.90	4.10
Q	3.30	3.50
U	5.20	5.40
V	2.90	3.10

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## ELECTRICAL CHARACTERISTICS

 $T_c=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$\text{V}_{\text{GS}} = 0\text{V}; \text{ID} = 250 \mu\text{A}$	650		V
$\text{V}_{\text{GS(th)}}$	Gate Threshold Voltage	$\text{V}_{\text{DS}} = \text{V}_{\text{GS}}; \text{ID} = 250 \mu\text{A}$	2.5	4.5	V
$\text{R}_{\text{DS(on)}}$	Drain-Source On-Resistance	$\text{V}_{\text{GS}} = 10\text{V}; \text{ID} = 6\text{A}$		300	$\text{m}\Omega$
$\text{I}_{\text{GSS}}$	Gate-Source Leakage Current	$\text{V}_{\text{GS}} = \pm 30\text{V}; \text{V}_{\text{DS}} = 0\text{V}$		$\pm 100$	nA
$\text{I}_{\text{DSS}}$	Drain-Source Leakage Current	$\text{V}_{\text{DS}} = \text{V}_{\text{DSS}}; \text{V}_{\text{GS}} = 0\text{V}$		5	$\mu\text{A}$
		$\text{V}_{\text{DS}} = \text{V}_{\text{DSS}}; \text{V}_{\text{GS}} = 0\text{V}; \text{T}_j = 125^\circ\text{C}$		50	
$\text{V}_{\text{SD}}$	Diode forward voltage	$\text{I}_F = 12\text{A}; \text{V}_{\text{GS}} = 0\text{V}$		1.4	V

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